

Maximum Ratings – Total Device (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Maximum Ratings N-CHANNEL – Q₁, 2N7002 Section (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ	V _{DGR}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Pulsed		±40	
Drain Current (Note 5)	I _D	115	mA
Continuous		73	
Continuous @ +100°C Pulsed		800	

Maximum Ratings P-CHANNEL – Q₂, BSS84 Section (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-50	V
Drain-Gate Voltage R _{GS} ≤ 20KΩ	V _{DGR}	-50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 5)	I _D	-130	mA

Note: 5. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Incorporated's suggested pad layout document, which can be found on our website at <http://www.diodes.com/package-outlines.html>.

Electrical Characteristics N-CHANNEL – Q₁, 2N7002 Section (@T_A = +25°C, unless otherwise specified.)

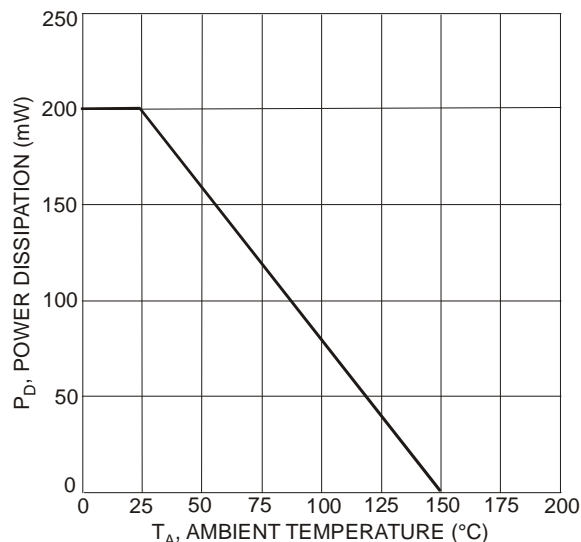
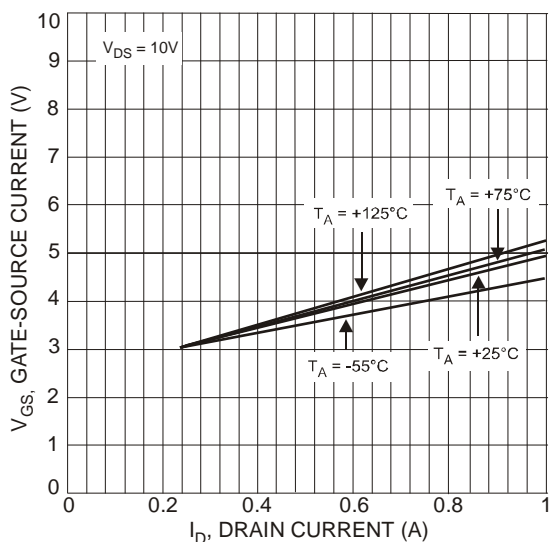
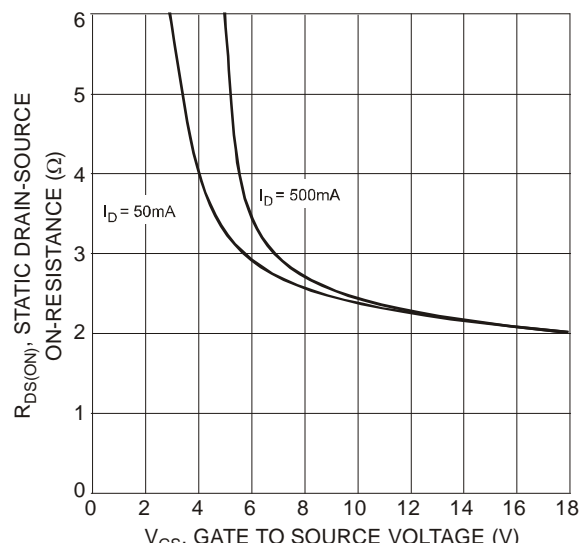
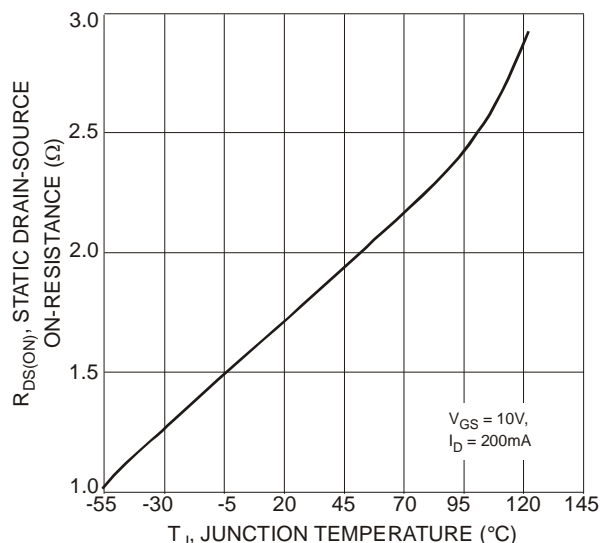
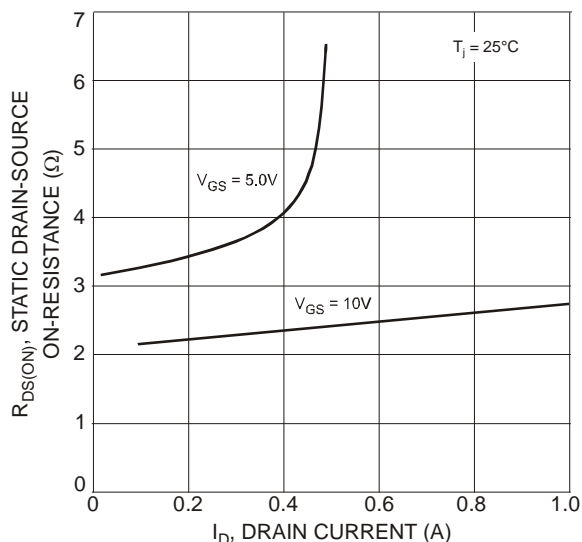
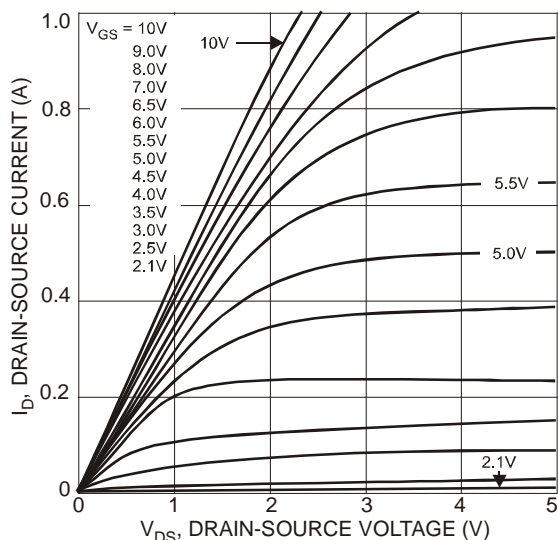
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current @ T _C = +25°C @ T _C = +125°C	I _{DSS}	—	—	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance @ T _J = +25°C @ T _J = +125°C	R _{DS(ON)}	—	3.2 4.4	7.5 13.5	Ω	V _{GS} = 5.0V, I _D = 0.05A V _{GS} = 10V, I _D = 0.5A
On-State Drain Current	I _{D(ON)}	0.5	1.0	—	A	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} =10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iSS}	—	22	50	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	11	25	pF	
Reverse Transfer Capacitance	C _{rSS}	—	2.0	5.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	7.0	20	ns	V _{DD} = 30V, I _D = 0.2A, R _L = 150Ω, V _{GEN} = 10V, R _{GEN} = 25Ω
Turn-Off Delay Time	t _{D(OFF)}	—	11	20	ns	

Electrical Characteristics P-CHANNEL – Q₂, BSS84 Section (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = +25°C
		—	—	-2	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = +125°C
		—	—	-100	nA	V _{DS} = -25V, V _{GS} = 0V, T _J = +25°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	-0.8	—	-2.0	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	10	Ω	V _{GS} = -5V, I _D = -0.100A
Forward Transconductance	g _{FS}	0.05	—	—	S	V _{DS} = -25V, I _D = -0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iSS}	—	—	45	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oSS}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rSS}	—	—	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = -30V, I _D = -0.27A, R _{GEN} = 50Ω, V _{GS} = -10V
Turn-Off Delay Time	t _{D(OFF)}	—	18	—	ns	

Note: 6. Short duration pulse test used to minimize self-heating effect.

N-CHANNEL – 2N7002 Section



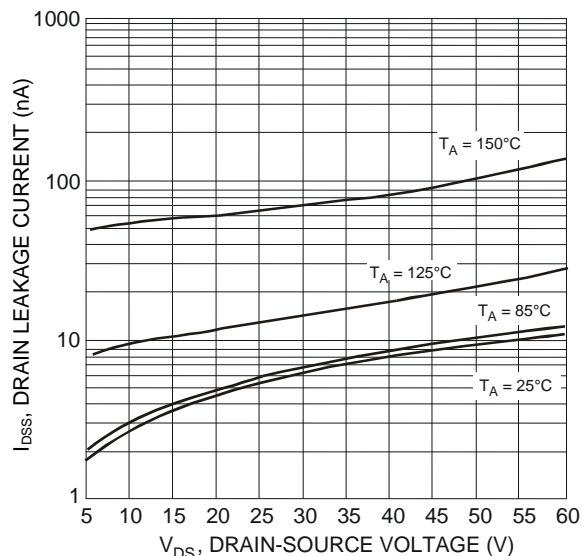


Figure 7 Typical Drain-Source Leakage Current vs. Voltage

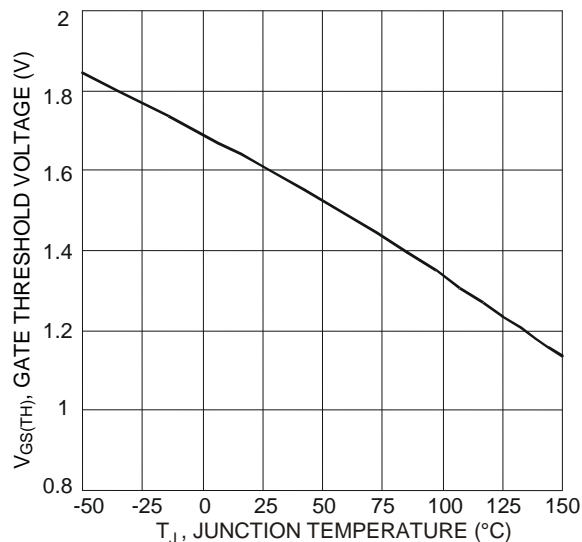


Figure 8 Gate Threshold Variation vs. Junction Temperature

P-CHANNEL – BSS84 Section

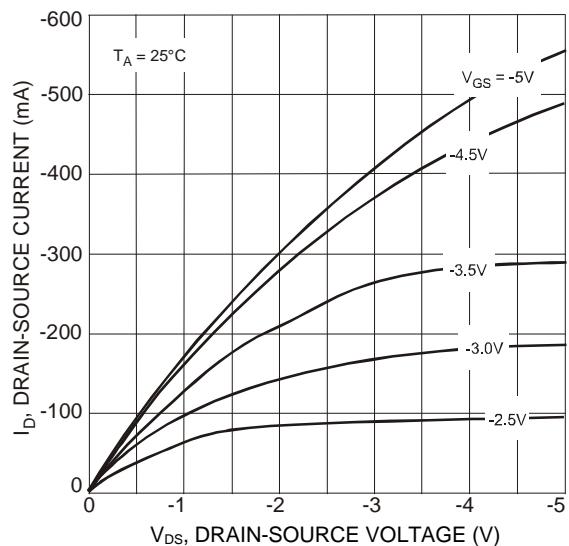


Figure 9 Drain-Source Current vs. Drain-Source Voltage

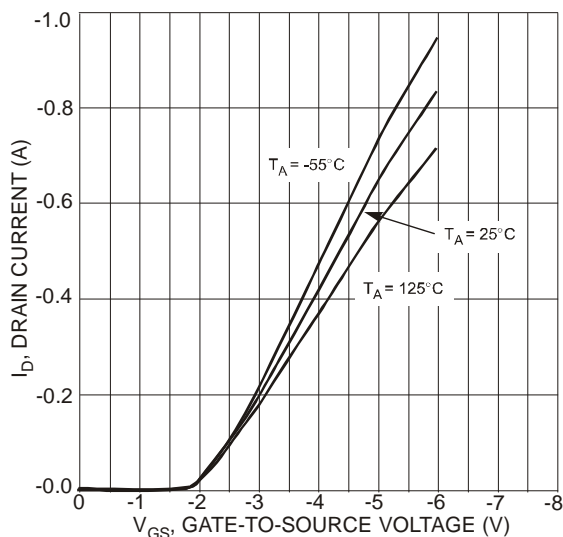


Figure 10 Drain Current vs. Gate-Source Voltage

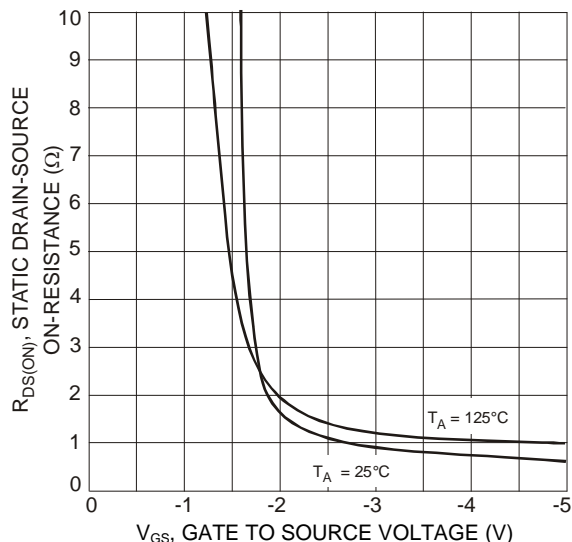


Figure 11 On-Resistance vs. Gate-Source Voltage

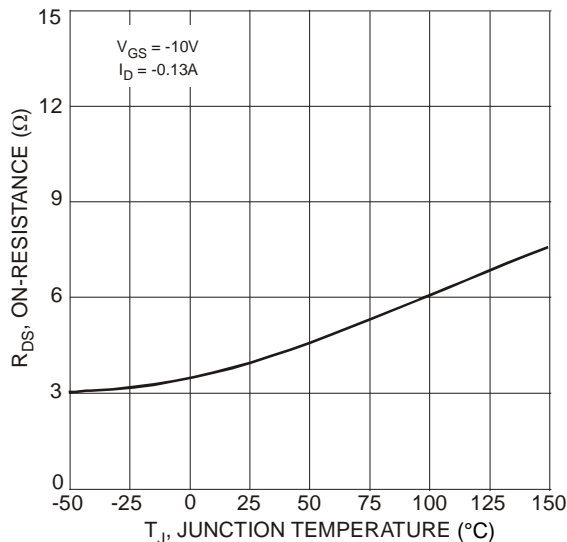


Figure 12 On-Resistance vs. Junction Temperature

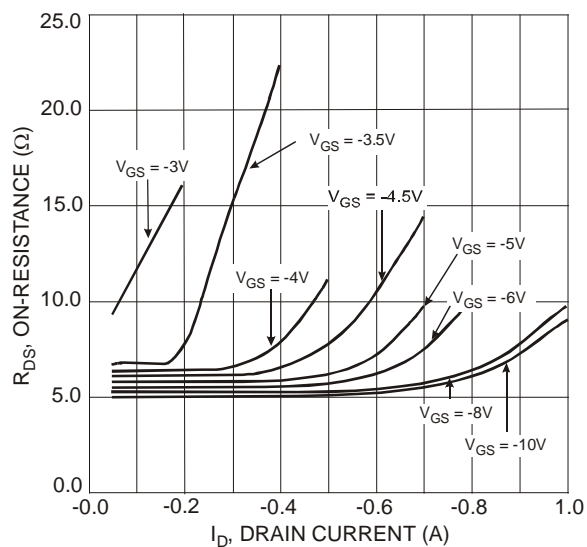


Figure 13 On-Resistance vs. Drain Current

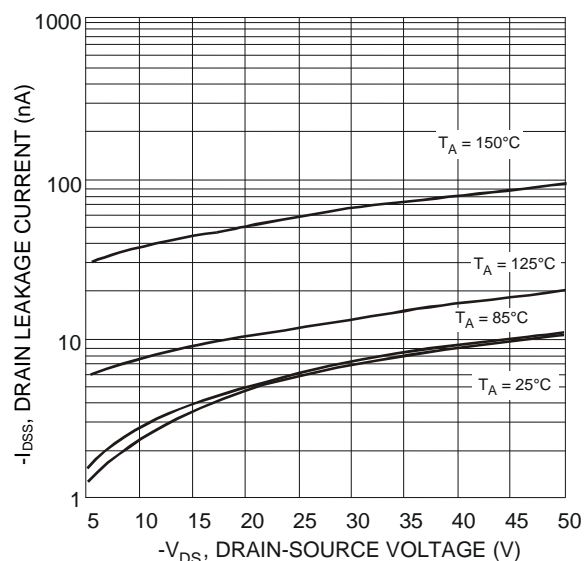


Figure 14 Typical Drain-Source Leakage Current vs. Voltage

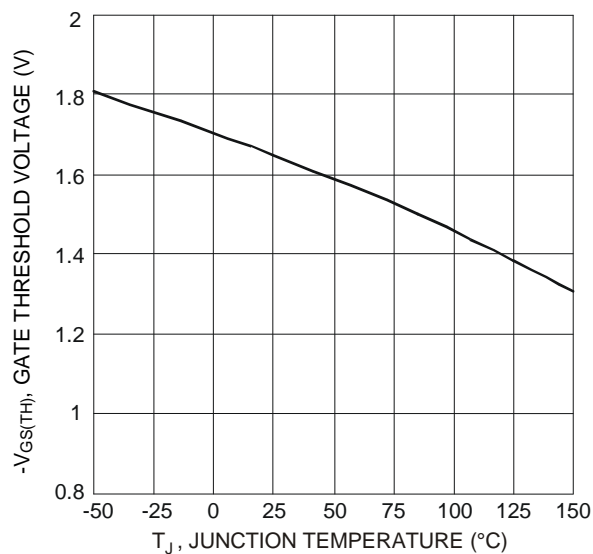
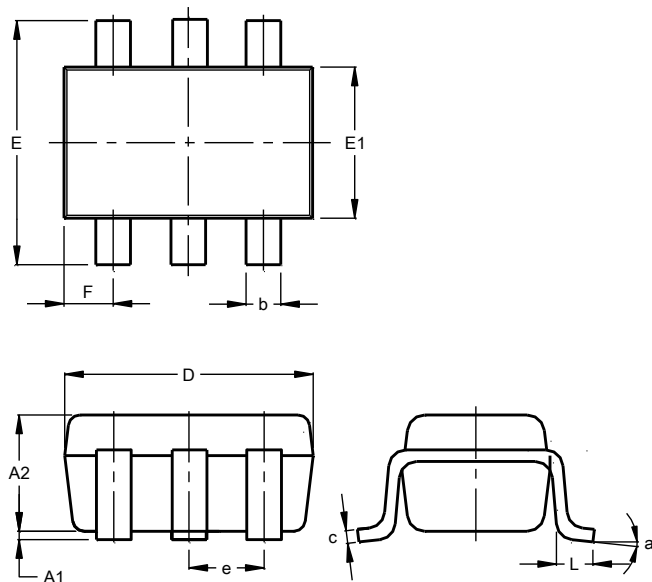


Figure 15 Gate Threshold Variation vs. Junction Temperature

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363

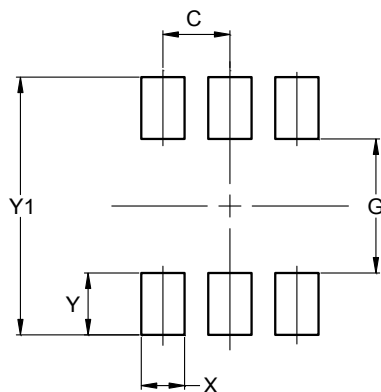


SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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